

***** Welcome to STN International *****

NEWS 1 Web Page URLs for STN Seminar Schedule - N. America
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 fields
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 Patent Office Classifications
 NEWS 6 AUG 02 The Analysis Edition of STN Express with Discover!
 (Version 7.01 for Windows) now available
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 NEWS 10 SEP 01 New pricing for the Save Answers for SciFinder Wizard within
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 NEWS 11 SEP 01 New display format, HITSTR, available in WPIDS/WPINDEX/WPIX
 NEWS 12 SEP 27 STANDARDS will no longer be available on STN
 NEWS 13 SEP 27 SWETSCAN will no longer be available on STN
 NEWS 14 OCT 28 KOREAPAT now available on STN

NEWS EXPRESS OCTOBER 29 CURRENT WINDOWS VERSION IS V7.01A, CURRENT
 MACINTOSH VERSION IS V6.0c(ENG) AND V6.0Jc(JP),
 AND CURRENT DISCOVER FILE IS DATED 11 AUGUST 2004

NEWS HOURS STN Operating Hours Plus Help Desk Availability
 NEWS INTER General Internet Information
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FILE 'HOME' ENTERED AT 15:24:35 ON 16 NOV 2004

=> file inspec		
COST IN U.S. DOLLARS	SINCE FILE	TOTAL
	ENTRY	SESSION
FULL ESTIMATED COST	0.21	0.21

FILE 'INSPEC' ENTERED AT 15:24:47 ON 16 NOV 2004
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FILE LAST UPDATED: 15 NOV 2004 <20041115/UP>
 FILE COVERS 1969 TO DATE.

<<< SIMULTANEOUS LEFT AND RIGHT TRUNCATION AVAILABLE IN
 THE BASIC INDEX >>>

=> s intrinsic gallium nitride
 60140 INTRINSIC
 169893 GALLIUM
 29974 NITRIDE
 L1 1 INTRINSIC GALLIUM NITRIDE
 (INTRINSIC(W)GALLIUM(W)NITRIDE)

=> i ii

L IS NOT A RECOGNIZED COMMAND

The previous command name entered was not recognized by the system.
For a list of commands available to you in the current file, enter
"HELP COMMANDS" at an arrow prompt (=>).

=> d ii i

L1 ANSWER 1 OF 1 INSPEC (C) 2004 IEE on STN

Full Text	References
AN 1996:5330139 INSPEC DN B9609-2810D-002	
TI High field flashover strength of intrinsic gallium nitride and aluminum nitride in vacuum.	
AU Khan, M.A.; Chen, O. (APA Opt. Inc., Blaine, MN, USA); Sudarshan, T.S.; Gradinaru, G.	
SO Applied Physics Letters (8 July 1996) vol.69, no.2, p.254-6. 17 refs. Doc. No.: S0003-6951(96)03128-2	
Published by: AIP	
Price: CCCC 0003-6951/96/69(2)/254/3/\$10.00	
CODEN: APPLAB ISSN: 0003-6951	
SICI: 0003-6951(19960708)69:2L:254:HFFS;1-G	
DT Journal	
TC Experimental	
CY United States	
LA English	

AN 1996:5330139 INSPEC DN B9609-2810D-002

TI High field flashover strength of intrinsic gallium nitride and aluminum nitride in vacuum.

AU Khan, M.A.; Chen, O. (APA Opt. Inc., Blaine, MN, USA); Sudarshan, T.S.; Gradinaru, G.

SO Applied Physics Letters (8 July 1996) vol.69, no.2, p.254-6. 17 refs.
Doc. No.: S0003-6951(96)03128-2

Published by: AIP

Price: CCCC 0003-6951/96/69(2)/254/3/\$10.00

CODEN: APPLAB ISSN: 0003-6951

SICI: 0003-6951(19960708)69:2L:254:HFFS;1-G

DT Journal

TC Experimental

CY United States

LA English

=> s semi-insulating gallium nitride

69288 SEMI

53254 INSULATING

169893 GALLIUM

29974 NITRIDE

L2 0 SEMI-INSULATING GALLIUM NITRIDE
(SEMI(W) INSULATING(W) GALLIUM(W) NITRIDE)

=> s semi insulating gallium nitride

69288 SEMI

53254 INSULATING

169893 GALLIUM

29974 NITRIDE

L3 0 SEMI INSULATING GALLIUM NITRIDE
(SEMI(W) INSULATING(W) GALLIUM(W) NITRIDE)

=> s semiinsulating gallium nitride

1616 SEMIINSULATING

169893 GALLIUM

29974 NITRIDE

L4 0 SEMIINSULATING GALLIUM NITRIDE
(SEMIINSULATING(W) GALLIUM(W) NITRIDE)

=> log y

COST IN U.S. DOLLARS

SINCE FILE

TOTAL

ENTRY

SESSION

FULL ESTIMATED COST

5.79

6.00

STN INTERNATIONAL LOGOFF AT 15:26:24 ON 16 NOV 2004

***** Welcome to STN International *****

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NEWS 6 AUG 02 The Analysis Edition of STN Express with Discover!
 (Version 7.01 for Windows) now available
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 status data from INPADOC
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 STN Express with Discover!
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NEWS 12 SEP 27 STANDARDS will no longer be available on STN
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NEWS 14 OCT 28 KOREAPAT now available on STN

NEWS EXPRESS OCTOBER 29 CURRENT WINDOWS VERSION IS V7.01A, CURRENT
 MACINTOSH VERSION IS V6.0c(ENG) AND V6.0Jc(JP),
 AND CURRENT DISCOVER FILE IS DATED 11 AUGUST 2004

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FILE 'HOME' ENTERED AT 17:18:09 ON 16 NOV 2004

=> file inspec

COST IN U.S. DOLLARS

SINCE FILE
ENTRY

TOTAL
SESSION

FULL ESTIMATED COST

0.21

0.21

FILE 'INSPEC' ENTERED AT 17:18:19 ON 16 NOV 2004

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FILE LAST UPDATED: 15 NOV 2004

<20041115/UP>

FILE COVERS 1969 TO DATE.

<<< SIMULTANEOUS LEFT AND RIGHT TRUNCATION AVAILABLE IN
THE BASIC INDEX >>>

=> s insulating gan

53254 INSULATING

16401 GAN

L1 63 INSULATING GAN

(INSULATING (W) GAN)

=> s transition metals

381004 TRANSITION

109725 METALS

L2 9497 TRANSITION METALS

(TRANSITION (W) METALS)

=> s l1 and l2

L3 0 L1 AND L2

=> d l1 1-63

L1 ANSWER 1 OF 63 INSPEC (C) 2004 IEE on STN



AN 2004:8130479 INSPEC DN A2004-22-7360L-032; B2004-11-2520D-051

TI Carrier and defect dynamics in photoexcited semi-insulating epitaxial GaN layers.

AU Gaubas, E.; Jursenas, S.; Miasojedovas, S.; Vaitkus, J.; Zukauskas, A.
(Inst. of Mater. Sci. & Appl. Res., Vilnius Univ., Lithuania)S0 Journal of Applied Physics (15 Oct. 2004) vol.96, no.8, p.4326-33. 22
refs.

Doc. No.: S0021-8979(04)08919-4

Published by: AIP

Price: CCCC 0021-8979/2004/96(8)/4326(8)/\$22.00

CODEN: JAPIAU ISSN: 0021-8979

SICI: 0021-8979(20041015)96:8L;4326:CDDP;1-Z

DT Journal

TC Theoretical; Experimental

CY United States

LA English

L1 ANSWER 2 OF 63 INSPEC (C) 2004 IEE on STN



AN 2004:8002079 INSPEC DN A2004-15-7360L-003; B2004-08-2550R-001
 TI Radiation-defect-dependent photoconductivity transients and photoluminescence in semi-insulating GaN.
 AU Gaubas, E. ; Kazlauskas, K. ; Tomasiunas, R. ; Vaitkus, J. ; Zukauskas, A. (Inst. of Mater. Sci. & Appl. Res., Vilnius Univ., Lithuania)
 SO Applied Physics Letters (21 June 2004) vol.84, no.25, p.5258-60. 12 refs.
 Doc. No. : S0003-6951(04)03425-4
 Published by: AIP
 Price: CCCC 0003-6951/2004/84(25)/5258(3)/\$20.00
 CODEN: APPLAB ISSN: 0003-6951
 SICI: 0003-6951(20040621)84:25L:5258:RDDP;1-Y
 DT Journal
 TC Experimental
 CY United States
 LA English

L1 ANSWER 3 OF 63 INSPEC (C) 2004 IEE on STN



AN 2004:7950820 INSPEC DN A2004-12-7360L-001; B2004-06-2550B-012
 TI Influence of high-temperature annealing on the properties of Fe doped semi-insulating GaN structures.
 AU Polyakov, A.Y. ; Smirnov, N.B. ; Govorkov, A.V. ; Shlensky, A.A. (Inst. of Rare Metals, Tolmachevsky, Russia); Pearton, S.J.
 SO Journal of Applied Physics (15 May 2004) vol.95, no.10, p.5591-6. 38 refs.
 Doc. No. : S0021-8979(04)02510-1
 Published by: AIP
 Price: CCCC 0021-8979/2004/95(10)/5591(6)/\$22.00
 CODEN: JAPIAU ISSN: 0021-8979
 SICI: 0021-8979(20040515)95:10L:5591:IHTA;1-K
 DT Journal
 TC Experimental
 CY United States
 LA English

L1 ANSWER 4 OF 63 INSPEC (C) 2004 IEE on STN



AN 2004:7926263 INSPEC DN B2004-05-2560S-035
 TI Enhancement of the electrical properties of AlGaIn/GaN HFETs by using undoped semi-insulating GaN.
 AU Jeong, Y.H. ; Oh, C.S. ; Shin, E.H. ; Kim, J.Y. ; Yang, J.W. ; Lim, K.Y. (Dept. of Semicond. Sci. & Technol., Chonbuk Nat. Univ., Chonju, South Korea)
 SO Journal of the Korean Physical Society (Jan. 2004) vol.44, no.1, p.140-3. 12 refs.
 Published by: Korean Phys. Soc
 CODEN: KPSJAS ISSN: 0374-4884
 SICI: 0374-4884(200401)44:1L:140:EEPA;1-R
 Conference: 10th Korean Conference on Semiconductors. Seoul, South Korea,

27-28 Feb 2003

DT Conference Article; Journal
TC Practical; Experimental
CY Korea, Democratic People's Republic of
LA English

L1 ANSWER 5 OF 63 INSPEC (C) 2004 IEE on STN

Full Text	References
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AN 2004:7909801 INSPEC DN A2004-09-8115H-015; B2004-05-0520F-004
TI Growth of semi-**insulating GaN** layer by controlling size of nucleation sites for SAW device applications.
AU Jae-Hoon Lee; Myoung-Bok Lee; Sung-Ho Hahm; Yong-Hyun Lee; Jung-Hee Lee (Sch. of Electron. Eng. & Comput. Sci., Kyungpook Nat. Univ., Daegu, South Korea); Young-Ho Bae; Hyun Kyung Cho
S0 MRS Internet Journal of Nitride Semiconductor Research (2003) vol.8S1. 17 refs.
Collection URL: <http://nsr.mij.mrs.org/>
Published by: Mater. Res. Soc
CODEN: MIJNF7 ISSN: 1092-5783
DT Journal
TC Practical; Experimental
CY United States
LA English

L1 ANSWER 6 OF 63 INSPEC (C) 2004 IEE on STN

Full Text	References
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AN 2004:7903841 INSPEC DN A2004-09-6320P-001
TI Ro-vibrational modes of H2 in 4H-SiC and 2H-GaN.
AU Eberlein, T.A.G.; Huggett, L.; Jones, R. (Sch. of Phys., Exeter Univ., UK); Briddon, P.R.
S0 Physica B (31 Dec. 2003) vol.340-342, p.171-4. 9 refs.
Published by: Elsevier
Price: CCCC 0921-4526/2003/\$30.00
CODEN: PHYBE3 ISSN: 0921-4526
SICI: 0921-4526(20031231)340/342L:171:VM;1-B
Conference: 22nd International Conference on Defects in Semiconductors - ICDS-22. Aarhus, Denmark, 28 July-1 Aug 2003
DT Conference Article; Journal
TC Theoretical
CY Netherlands
LA English

L1 ANSWER 7 OF 63 INSPEC (C) 2004 IEE on STN

Full Text	References
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AN 2004:7855798 INSPEC DN A2004-06-7360L-001; B2004-03-2520D-047
TI Properties of Fe-doped semi-**insulating GaN** structures.
AU Polyakov, A.Y.; Smirnov, N.B.; Govorkov, A.V. (Inst. of Rare Metals, Tolmachevsky, Russia); Pearton, S.J.

S0 Journal of Vacuum Science & Technology B (Microelectronics and Nanometer Structures) (Jan. 2004) vol.22, no.1, p.120-5. 37 refs.

Doc. No.: S0734-211X(04)03601-7

Published by: AIP for American Vacuum Soc

Price: CCCC 1071-1023/2004/22(1)/120/6/\$19.00

CODEN: JVTBD9 ISSN: 1071-1023

SICI: 1071-1023(200401)22:1L.120:PDSI;1-4

DT Journal

TC Experimental

CY United States

LA English

L1 ANSWER 8 OF 63 INSPEC (C) 2004 IEE on STN



AN 2004:7821192 INSPEC DN A2004-03-6630J-005

TI Hydrogen molecules in 4H-SiC and 2H-GaN.

AU Eberlein, T.A.G.; Huggett, L.; Jones, R. (Sch. of Phys., Exeter Univ., UK); Briddon, P.R.

S0 Journal of Physics: Condensed Matter (8 Oct. 2003) vol.15, no.39, p.S2897-902. 11 refs.

Doc. No.: S0953-8984(03)67271-1

Published by: IOP Publishing

Price: CCCC 0953-8984/03/392897+06\$30.00

CODEN: JCOMEL ISSN: 0953-8984

SICI: 0953-8984(20031008)15:39L.s2897:HM;1-A

Conference: Workshop on 'Physics of Group IV Materials'. Exeter, UK, 7-10 April 2003

DT Conference Article; Journal

TC Theoretical

CY United Kingdom

LA English

L1 ANSWER 9 OF 63 INSPEC (C) 2004 IEE on STN



AN 2003:7770510 INSPEC DN A2003-24-7360L-001; B2003-12-2520D-019

TI Electrical and optical properties of Fe-doped semi-insulating GaN templates.

AU Polyakov, A.Y.; Smirnov, N.B.; Govorkov, A.V. (Inst. of Rare Metals, Moscow, Russia); Pearton, S.J.

S0 Applied Physics Letters (20 Oct. 2003) vol.83, no.16, p.3314-16. 20 refs.

Doc. No.: S0003-6951(03)05042-3

Published by: AIP

Price: CCCC 01/03/6951/2003/83(16)/3314(3)/\$20.00

CODEN: APPLAB ISSN: 0003-6951

SICI: 0003-6951(20031020)83:16L.3314:EOPD;1-1

DT Journal

TC Experimental

CY United States

LA English

L1 ANSWER 10 OF 63 INSPEC (C) 2004 IEE on STN

Full Text Cited References

AN 2003:7756693 INSPEC DN A2003-23-8115H-005; B2003-11-0520F-075
 TI Role of potential barriers in epitaxial layers of semi-insulating GaN layers.
 AU Vaitkus, J.V.; Gaubas, E. (Inst. of Mater. Sci. & Appl. Res., Vilnius Univ., Lithuania); Sakai, S.; Lacroix, Y.; Tao Wang; Smith, K.M.; Rahman, M.; Cunningham, W.
 S0 Diffusion and Defect Data Part B (Solid State Phenomena) (2003) vol.93, p.301-6. 12 refs.
 Published by: Balaban Publishers; Scitec Publications
 CODEN: DDBPE8 ISSN: 1012-0394
 SICI: 1012-0394(2003)93L:301:RPBE;1-Y
 DT Journal
 TC Experimental
 CY Switzerland
 LA English

L1 ANSWER 11 OF 63 INSPEC (C) 2004 IEE on STN

Full Text Cited References

AN 2003:7741695 INSPEC DN A2003-21-7220P-002
 TI Thermoelectric effect spectroscopy measurements on semi-insulating GaN.
 AU Pavlovic, M.; Desnica, U.V. (Ruder Boskovic Inst., Zagreb, Croatia); Fang, Z.-Q.; Look, D.C.
 S0 Vacuum (9 May 2003) vol.71, no.1-2, p.153-8. 28 refs.
 Published by: Elsevier
 Price: CCCC 0042-207X/03/\$30.00
 CODEN: VACUAV ISSN: 0042-207X
 SICI: 0042-207X(20030509)71:1/2L:153:TESM;1-R
 Conference: 9th Joint Vacuum Conference (JVC-9). Schloss Seggau, Austria, 16-20 June 2002
 DT Conference Article; Journal
 TC Experimental
 CY United Kingdom
 LA English

L1 ANSWER 12 OF 63 INSPEC (C) 2004 IEE on STN

Full Text Cited References

AN 2003:7728893 INSPEC DN A2003-20-7320D-040; B2003-10-2520D-045
 TI Two-dimensional electron gases induced by polarization charges in AlN/GaN heterostructure grown by plasma-assisted molecular-beam epitaxy.
 AU Jeganathan, K.; Ide, T.; Shimizu, M.; Okumura, H. (Power Electron. Res. Center, Nat. Inst. of Adv. Ind. Sci. & Technol., Ibaraki, Japan)
 S0 Journal of Applied Physics (1 Sept. 2003) vol.94, no.5, p.3260-3. 18 refs.
 Doc. No.: S0021-8979(03)07218-9
 Published by: AIP
 Price: CCCC 0021-8979/2003/94(5)/3260(4)/\$20.00

CODEN: JAPIAU ISSN: 0021-8979
SICI: 0021-8979(20030901)94:5L:3260:DEGI;1-R

DT Journal
TC Experimental
CY United States
LA English

L1 ANSWER 13 OF 63 INSPEC (C) 2004 IEE on STN

Full Text	Cited References
--------------	---------------------

AN 2003:7723750 INSPEC DN A2003-20-7860H-005; B2003-10-4220-016
TI Luminescence properties of charged dislocations in semi-insulating GaN:Zn.
AU Srinivasan, S.; Cai, J.; Contreras, O.; Ponce, F.A. (Dept. of Phys. &
Astron., Arizona State Univ., Tempe, AZ, USA); Look, D.C.; Molnar, R.J.
S0 Physica Status Solidi C (2002) no.1, p.508-11. 7 refs.
Published by: Wiley-VCH
Price: CCCC 1610-1634/02/00012-0508\$17.50+.50/0
CODEN: PSSCGL ISSN: 1610-1634
SICI: 1610-1634(2002)1L:508:LPCD;1-G
Conference: International Workshop on Nitride Semiconductors (IWN 2002).
Aachen, Germany, 22-25 July 2002

DT Conference Article; Journal
TC Experimental
CY Germany, Federal Republic of
LA English

L1 ANSWER 14 OF 63 INSPEC (C) 2004 IEE on STN

Full Text	Cited References
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AN 2003:7653110 INSPEC DN A2003-14-7240-011; B2003-07-4210-017
TI Deep-defect-induced quenching effects in semi-insulating GaN layers
detected by photoelectrical spectroscopic techniques.
AU Witte, H.; Krtschil, A.; Lisker, M.; Schrenk, E.; Christen, J.; Krost, A.
(Inst. of Exp. Phys., Otto-von-Guericke-Univ., Magdeburg, Germany); Kuhn,
B.; Scholz, F.
S0 Applied Physics Letters (9 June 2003) vol.82, no.23, p.4083-5. 16 refs.
Published by: AIP
Price: CCCC 01/03/6951/2003/82(23)/4083(3)/\$20.00
CODEN: APPLAB ISSN: 0003-6951
SICI: 0003-6951(20030609)82:23L:4083:DDIQ;1-V

DT Journal
TC Experimental
CY United States
LA English

L1 ANSWER 15 OF 63 INSPEC (C) 2004 IEE on STN

Full Text	Cited References
--------------	---------------------

AN 2003:7650116 INSPEC DN B2003-07-0520F-069
TI Engineering of an insulating buffer and use of AlN interlayers: two
optimisations for AlGaIn-GaN HEMT-like structures.

AU Bougrioua, Z. (CRHEA, CNRS, Valbonne, France); Moerman, I.; Nistor, L.;
Van Daele, B.; Monroy, E.; Palacios, T.; Calle, F.; Leroux, M.
S0 Physica Status Solidi C (2003) no.3, p.93-100. 12 refs.
Published by: Wiley-VCH
Price: CCCC 0031-8965/03/19501-0093\$17.50+.50/0
ISSN: 1610-1634
SICI: 1610-1634(2003)3L:93:EIBI;1-0
DT Journal
TC Practical; Experimental
CY Germany, Federal Republic of
LA English

L1 ANSWER 16 OF 63 INSPEC (C) 2004 IEE on STN

[Full Text](#) [References](#)

AN 2003:7583016 INSPEC DN A2003-10-7125T-005; B2003-05-2520D-046
TI The franz-keldysh effect in shocked GaN:Mg.
AU Peng, H.Y.; McCluskey, M.D.; Gupta, Y.M. (Dept. of Phys., Washington State
Univ., Pullman, WA, USA); Kneissl, M.; Johnson, N.M.
S0 Applied Physics Letters (31 March 2003) vol.82, no.13, p.2085-7. 23 refs.
Published by: AIP
Price: CCCC 01/03/6951/2003/82(13)/2085(3)/\$19.00
CODEN: APPLAB ISSN: 0003-6951
SICI: 0003-6951(20030331)82:13L:2085:FKES;1-I
DT Journal
TC Experimental
CY United States
LA English

L1 ANSWER 17 OF 63 INSPEC (C) 2004 IEE on STN

[Full Text](#) [References](#)

AN 2003:7562747 INSPEC DN A2003-09-6855-004; B2003-04-2520D-063
TI Growth of Fe doped semi-insulating GaN by metalorganic chemical vapor
deposition.
AU Heikman, S.; Keller, S.; DenBaars, S.P.; Mishra, U.K. (Dept. of Electr. &
Comput. Eng., California Univ., Santa Barbara, CA, USA)
S0 Applied Physics Letters (15 July 2002) vol.81, no.3, p.439-41. 28 refs.
Doc. No.: S0003-6951(02)01826-0
Published by: AIP
Price: CCCC 01/03/6951/2002/81(3)/439(3)/\$19.00
CODEN: APPLAB ISSN: 0003-6951
SICI: 0003-6951(20020715)81:3L:439:GDSI;1-T
DT Journal
TC Experimental
CY United States
LA English

L1 ANSWER 18 OF 63 INSPEC (C) 2004 IEE on STN

[Full Text](#) [References](#)

AN 2003:7555977 INSPEC DN A2003-08-7855-037
 TI Annealing effect on the Al⁺ implantation induced deep traps in GaN film.
 AU Xu Xiao-liang; He Hai-yan; Liu Hong-tu; Shi Chao-shu (Struct. Res. Lab., Univ. of Sci. & Technol. of China, Hefei, China); Ge Wei-kun; Luo, E. Z.; Sundaravel, B.; Wilson, I.H.
 SO Chinese Journal of Liquid Crystals and Displays (Aug. 2002) vol.17, no.4, p.243-52. 22 refs.
 Published by: Science Press
 ISSN: 1007-2780
 SICI: 1007-2780(200208)17:4L.243:AEII;1-8
 DT Journal
 TC Experimental
 CY China
 LA Chinese

L1 ANSWER 19 OF 63 INSPEC (C) 2004 IEE on STN



AN 2003:7501464 INSPEC DN A2003-04-6855-046; B2003-02-2560S-018
 TI Comparison of high mobility AlGa_N/Ga_N heterostructures grown by MBE on HVPE Ga_N templates and directly nucleated on sapphire.
 AU Manfra, M. J.; Weimann, N. G.; Hsu, J. W. P.; Pfeiffer, L. N.; West, K. W. (Lucent Technol. Bell Labs., Murray Hill, NJ, USA); Molnar, R. J.
 SO 2002 International Conference on Molecular Beam Epitaxy (Cat. No.02EX607) Piscataway, NJ, USA: IEEE, 2002. p.231-2 of 424 pp.
 Conference: San Francisco, CA, USA, 15-20 Sept 2002
 Sponsor(s): IEEE Lasers & Electro-Opt. Soc
 Price: CCCC 0-7803-7581-5/02/\$17.00
 ISBN: 0-7803-7581-5
 DT Conference Article
 TC Experimental
 CY United States
 LA English

L1 ANSWER 20 OF 63 INSPEC (C) 2004 IEE on STN



AN 2003:7490791 INSPEC DN A2003-03-7240-006; B2003-02-4210-007
 TI Photo-stimulated current spectroscopy and its application in detecting aluminum implantation-induced deep traps in GaN.
 AU Xiaoliang Xu; Haiyan He; Hongtu Liu; Chaoshu Shi (Struct. Res. Lab., Acad. Sinica, Hefei, China); Weikun Ge; Luo, E. Z.; Sundaravel, B.; Wilson, I.H.
 SO Thin Solid Films (2 Sept. 2002) vol.416, no.1-2, p.294-301. 31 refs.
 Doc. No.: S0040-6090(02)00681-8
 Published by: Elsevier
 Price: CCCC 0040-6090/02/\$22.00
 CODEN: THSFAP ISSN: 0040-6090
 SICI: 0040-6090(20020902)416:1/2L.294:PSCS;1-Y
 DT Journal
 TC Experimental
 CY Switzerland

LA English

L1 ANSWER 21 OF 63 INSPEC (C) 2004 IEE on STN

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AN 2002:7453703 INSPEC DN B2002-12-2560S-026

TI Characterization of GaN based MESFETs by comparing electroluminescence, photoionization and cathodoluminescence spectroscopy.

AU Armani, N. (Ist. MASPEC, CNR, Parma, Italy); Chini, A.; Manfredi, M.; Meneghesso, G.; Pavesi, M.; Grillo, V.; Salviati, G.; Zanoni, E.

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Bristol, UK: IOP Publishing, 2001. p.503-6 of xiv+610 pp. 11 refs.

Conference: Oxford, UK, 25-29 March 2001

ISBN: 0-7503-0818-4

DT Conference Article

TC Practical; Experimental

CY United Kingdom

LA English

L1 ANSWER 22 OF 63 INSPEC (C) 2004 IEE on STN

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AN 2002:7399617 INSPEC DN A2002-22-7155-003; B2002-11-2520D-019

TI Thermoelectric effect spectroscopy of deep levels in semi-insulating GaN.

AU Desnica, U.V.; Pavlovic, M. (Boskovic (R.) Inst., Zagreb, Croatia); Fang, Z.-Q.; Look, D.C.

S0 Journal of Applied Physics (1 Oct. 2002) vol.92, no.7, p.4126-8. 28 refs.

Doc. No.: S0021-8979(02)08919-3

Published by: AIP

Price: CCCC 0021-8979/2002/92(7)/4126(3)/\$19.00

CODEN: JAPIAU ISSN: 0021-8979

SICI: 0021-8979(20021001)92:7L:4126:TESD;1-H

DT Journal

TC Experimental

CY United States

LA English

L1 ANSWER 23 OF 63 INSPEC (C) 2004 IEE on STN

Full Text Citings
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AN 2002:7383461 INSPEC DN A2002-21-7340L-005; B2002-10-2530B-027

TI High mobility AlGaIn/GaN heterostructures grown by plasma-assisted molecular beam epitaxy on semi-insulating GaN templates prepared by hydride vapor phase epitaxy.

AU Manfra, M.J.; Weimann, N.G.; Hsu, J.W.P.; Pfeiffer, L.N.; West, K.W. (Lucent Technol. Bell Labs., Murray Hill, NJ, USA); Syed, S.; Stormer, H.L.; Pan, W.; Lang, D.V.; Chu, S.N.G.; Kowach, G.; Sergent, A.M.; Caissie, J.; Molvar, K.M.; Mahoney, L.J.; Molnar, R.J.

S0 Journal of Applied Physics (1 July 2002) vol.92, no.1, p.338-45. 15 refs.

Doc. No. : S0021-8979(02)03414-X
Published by: AIP
Price: CCCC 0021-8979/2002/92(1)/338(8)/\$19.00
CODEN: JAPIAU ISSN: 0021-8979
SICI: 0021-8979(20020701)92:1L 338:HMAH;1-#

DT Journal
TC Experimental
CY United States
LA English

L1 ANSWER 24 OF 63 INSPEC (C) 2004 IEE on STN

[Full Text](#) [References](#)

AN 2002:7380070 INSPEC DN A2002-21-7865K-006; B2002-10-2520D-049
TI Optical metastability in undoped GaN grown on Ga-rich GaN buffer layers.
AU Dhar, S.; Ghosh, S. (Sch. of Phys. Sci., Jawaharlal Nehru Univ., New Delhi, India)
S0 Applied Physics Letters (17 June 2002) vol.80, no.24, p.4519-21. 24 refs.
Doc. No. : S0003-6951(02)06221-6
Published by: AIP
Price: CCCC 0003-6951/2002/80(24)/4519(3)/\$19.00
CODEN: APPLAB ISSN: 0003-6951
SICI: 0003-6951(20020617)80:24L 4519:OMUG;1-I

DT Journal
TC Experimental
CY United States
LA English

L1 ANSWER 25 OF 63 INSPEC (C) 2004 IEE on STN

[Full Text](#) [References](#)

AN 2002:7367591 INSPEC DN A2002-20-8115G-008; B2002-10-2530B-006
TI Dislocation and morphology control during molecular-beam epitaxy of AlGaIn/GaN heterostructures directly on sapphire substrates.
AU Manfra, M.J.; Weimann, N.G.; Hsu, J.W.P.; Pfeiffer, L.N.; West, K.W. (Lucent Technol. Bell Labs., Murray Hill, NJ, USA); Chu, S.N.G.
S0 Applied Physics Letters (19 Aug. 2002) vol.81, no.8, p.1456-8. 9 refs.
Doc. No. : S0003-6951(02)04731-9
Published by: AIP
Price: CCCC 0003-6951/2002/81(8)/1456(3)/\$19.00
CODEN: APPLAB ISSN: 0003-6951
SICI: 0003-6951(20020819)81:8L 1456:DMCD;1-2

DT Journal
TC Experimental
CY United States
LA English

L1 ANSWER 26 OF 63 INSPEC (C) 2004 IEE on STN

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AN 2002:7348972 INSPEC DN A2002-18-7865K-045

TI Optical study of GaN doped with Mn grown by metal organic vapor phase epitaxy.
 AU Korotkov, R.Y.; Gregie, J.M.; Wessels, B.W. (Dept. of Mater. Sci. & Eng., Northwestern Univ., Evanston, IL, USA)
 SO GaN and Related Alloys - 2000. Symposium (Materials Research Society Symposium Proceedings Vol.639)
 Editor(s): Wetzol, C.; Shur, M.S.; Mishra, U.K.; Gil, B.; Kishino, K.
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 Conference: Boston, MA, USA, 27 Nov-1 Dec 2000
 DT Conference Article
 TC Experimental
 CY United States
 LA English

L1 ANSWER 27 OF 63 INSPEC (C) 2004 IEE on STN

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AN 2002:7166632 INSPEC DN A2002-05-7340L-014; B2002-03-2560S-010
 TI Back bias effects in AlGaIn/GaN HFETs.
 AU Uren, M.J.; Herbert, D.; Martin, T.; Hughes, B.T.; Birbeck, J.; Balmer, R.; Pidduck, A.J. (QinetiQ Ltd., Malvern, UK); Jones, S.K.
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 Published by: Wiley-VCH
 Price: CCCC 0031-8965/01/18811-0195\$17.50+.50/0
 CODEN: PSSABA ISSN: 0031-8965
 SIC1: 0031-8965(20011116)188:1L.195:BBA;1-7
 Conference: Fourth International Conference on Nitride Semiconductors.
 Denver, CO, USA, 16-20 July 2001
 DT Conference Article; Journal
 TC Practical; Experimental
 CY Germany, Federal Republic of
 LA English

L1 ANSWER 28 OF 63 INSPEC (C) 2004 IEE on STN

[Full Text](#) [References](#)

AN 2002:7159990 INSPEC DN A2002-05-8115G-012; B2002-02-0520D-053
 TI Growth and characterisation of high electron mobility transistors on 4H-SiC by ammonia molecular beam epitaxy.
 AU Webb, J.; Haipeng Tang; Bardwell, J.A.; Rolfe, S.; Ying Liu; Lapointe, A.; Marshall, P. (Inst. for Microstructural Sci., Nat. Res. Council of Canada, Ottawa, Ont., Canada); MacElwee, T.W.
 SO Physica Status Solidi A (16 Nov. 2001) vol.188, no.1, p.271-4. 9 refs.
 Published by: Wiley-VCH
 Price: CCCC 0031-8965/01/18811-0271\$17.50+.5010
 CODEN: PSSABA ISSN: 0031-8965
 SIC1: 0031-8965(20011116)188:1L.271:GCHE;1-Q
 Conference: Fourth International Conference on Nitride Semiconductors.
 Denver, CO, USA, 16-20 July 2001
 DT Conference Article; Journal

TC Experimental
CY Germany, Federal Republic of
LA English

L1 ANSWER 29 OF 63 INSPEC (C) 2004 IEE on STN

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AN 2002:7143723 INSPEC DN A2002-04-7320D-011; B2002-02-2530B-020
TI 2DEG characteristics of AlN/GaN heterointerface on sapphire substrates grown by plasma-assisted MBE.
AU Jeganathan, K.; Ide, T.; Shen, S.X.Q.; Shimizu, M.; Okumura, H. (Power Electron. Res. Center, Nat. Inst. of Adv. Ind. Sci. & Technol., Ibaraki, Japan)
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Price: CCCC 0370-1972/01/22811-0613\$17.50+.50/0
CODEN: PSSBBD ISSN: 0370-1972
SICI: 0370-1972(20011101)228:2L.613:2CHS;1-U
Conference: Fourth International Conference on Nitride Semiconductors. Denver, CO, USA, 16-20 July 2001
DT Conference Article; Journal
TC Experimental
CY Germany, Federal Republic of
LA English

L1 ANSWER 30 OF 63 INSPEC (C) 2004 IEE on STN

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AN 2002:7137121 INSPEC DN B2002-02-2560S-013
TI Fabrication and characterization of GaN junction field effect transistors.
AU Zhang, L. (Sandia Nat. Labs., Albuquerque, NM, USA); Lester, L.F.; Baca, A.G.; Shul, R.J.; Chang, P.C.; Willison, C.G.; Mishra, U.K.; Denbaars, S.P.; Zolper, J.C.
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Conference: Boston, MA, USA, 28 Nov-3 Dec 1999
ISBN: 1-55899-503-X
DT Conference Article
TC Experimental; Practical
CY United States
LA English

L1 ANSWER 31 OF 63 INSPEC (C) 2004 IEE on STN

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AN 2001:7011094 INSPEC DN A2001-18-6855-086; B2001-09-0520F-088
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AU Smart, J.A. (Dept. of Electr. Eng., Cornell Univ., Ithaca, NY, USA);
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S0 WOCSDICE 2000. 24th Workshop on Compound Semiconductor Devices and
Integrated Circuits
Ann Arbor, MI, USA: Univ. Michigan, 2000. p.1-5, 1-6 of xxii+196 pp. 1
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Conference: Aegean Sea, Greece, 29 May-2 June 2000
ISBN: 0-9703111-0-9
DT Conference Article
TC Practical; Experimental
CY United States
LA English

L1 ANSWER 32 OF 63 INSPEC (C) 2004 IEE on STN

Full Text	Citing References
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AN 2001:6991427 INSPEC DN A2001-17-8115G-035; B2001-09-0520D-045
TI Advances in III-nitride growth by ammonia-MBE.
AU Webb, J.B.; Tang, H.; Bardwell, J.A. (Inst. for Microstructural Sci., Nat.
Res. Council of Canada, Ottawa, Ont., Canada)
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Tokyo, Japan: Inst. Pure & Appl. Phys, 2000. p.228-32 of 1002 pp. 9 refs.
Conference: Nagoya, Japan, 24-27 Sept 2000
Sponsor(s): Japan Soc. Appl. Phys.; Japan Soc. Promotion of Sci
ISBN: 4-900526-13-4
DT Conference Article
TC General Review; Experimental; Practical
CY Japan
LA English

L1 ANSWER 33 OF 63 INSPEC (C) 2004 IEE on STN

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AN 2001:6932166 INSPEC DN B2001-07-2560S-001
TI Effect of growth termination conditions on the performance of AlGaIn/GaN
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AU Keller, S.; Vetury, R.; Parish, G.; DenBaars, S.P.; Mishra, U.K. (Dept.
Electr. & Comput. Eng., California Univ., Santa Barbara, CA, USA)
S0 Applied Physics Letters (14 May 2001) vol.78, no.20, p.3088-90. 14 refs.
Doc. No.: S0003-6951(01)05420-1
Published by: AIP
Price: CCCC 0003-6951/2001/78(20)/3088(3)/\$18.00
CODEN: APPLAB ISSN: 0003-6951
SICI: 0003-6951(20010514)78:20L:3088:EGTC;1-L
DT Journal
TC Experimental
CY United States
LA English

L1 ANSWER 34 OF 63 INSPEC (C) 2004 IEE on STN



AN 2000:6795326 INSPEC DN B2001-02-1350F-014
 TI Recessed-gate GaN MESFET using ICP-RIE for high temperature microwave applications.
 AU Lee, C.; Lu, W. (Dept. of Electr. & Comput. Eng., Illinois Univ., Urbana, IL, USA); Piner, E.; Adesida, I.
 SO 58th DRC. Device Research Conference. Conference Digest (Cat. No. 00TH8526) Piscataway, NJ, USA: IEEE, 2000. p.41-2 of xii+176 pp. 6 refs.
 Conference: Denver, CO, USA, 19-21 June 2000
 Sponsor(s): IEEE Electron Devices Soc
 ISBN: 0-7803-6472-4
 DT Conference Article
 TC Application; Practical; Experimental
 CY United States
 LA English

L1 ANSWER 35 OF 63 INSPEC (C) 2004 FIZ KARLSRUHE on STN



AN 2000:6766620 INSPEC DN A2001-01-7830-012
 TI Infrared studies on GaN single crystals and homoepitaxial layers.
 AU Frayssinet, E.; Knap, W. (Groupe d'Etudes des Semicond., CNRS, Montpellier, France); Prystawko, P.; Leszczynski, M.; Grzegory, I.; Suski, T.; Beaumont, B.; Gibart, P.
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 Doc. No.: S0022-0248(00)00537-6
 Published by: Elsevier
 Price: CCCC 0022-0248/2000/\$20.00
 CODEN: JCRGAE ISSN: 0022-0248
 SICI: 0022-0248(200009)218:2/4L.161:ISSC;1-0
 DT Journal
 TC Experimental
 CY Netherlands
 LA English

L1 ANSWER 36 OF 63 INSPEC (C) 2004 IEE on STN



AN 2000:6572341 INSPEC DN A2000-11-6855-060; B2000-06-0520J-004
 TI Near defect free GaN substrates.
 AU Porowski, S. (High Pressure Res. Center, Acad. of Sci., Warsaw, Poland)
 SO GaN and Related Alloys. Symposium
 Editor(s): Pearton, S.J.; Kuo, C.; Wright, A.F.; Uenoyama, T.
 Warrendale, PA, USA: Mater. Res. Soc, 1999. p.G1.3/11 pp. of 1028 pp. 37 refs.
 Conference: Boston, MA, USA, 30 Nov-4 Dec 1998
 ISBN: 1-55899-443-2
 DT Conference Article
 TC Experimental
 CY United States

LA English

L1 ANSWER 37 OF 63 INSPEC (C) 2004 IEE on STN

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AN 2000:6540346 INSPEC DN B2000-05-1350F-005

TI Epitaxially-grown GaN junction field effect transistors.

AU Zhang, L. (Sandia Nat. Labs., Albuquerque, NM, USA); Lester, L.F.; Baca, A.G.; Shul, R.J.; Chang, P.C.; Willison, C.G.; Mishra, U.K.; Denbaars, S.P.; Zolper, J.C.

S0 IEEE Transactions on Electron Devices (March 2000) vol.47, no.3, p.507-11. 25 refs.

Doc. No.: S0018-9383(00)01938-9

Published by: IEEE

Price: CCCC 0018-9383/2000/\$10.00

CODEN: IETDAI ISSN: 0018-9383

SICI: 0018-9383(200003)47:3L:507:EGJF;1-4

DT Journal

TC Application; Practical; Experimental

CY United States

LA English

L1 ANSWER 38 OF 63 INSPEC (C) 2004 IEE on STN

[Full Text](#) [Cited References](#)

AN 1999:6410037 INSPEC DN A2000-01-8115J-001; B2000-01-0520X-001

TI **Insulating GaN**:Zn layers grown by hydride vapor phase epitaxy on SiC substrates.

AU Kuznetsov, N.I.; Nikolaev, A.E.; Zubrilov, A.S. (A.F. Ioffe Physicotech. Inst., Acad. of Sci., St. Petersburg, Russia); Melnik, Yu.V.; Dmitriev, V.A.

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Doc. No.: S0003-6951(99)03446-4

Published by: AIP

Price: CCCC 0003-6951/99/75(20)/3138(3)/\$15.00

CODEN: APPLAB ISSN: 0003-6951

SICI: 0003-6951(19991115)75:20L:3138:ILGH;1-T

DT Journal

TC Experimental

CY United States

LA English

L1 ANSWER 39 OF 63 INSPEC (C) 2004 IEE on STN

[Full Text](#) [Cited References](#)

AN 1999:6402056 INSPEC DN A1999-24-8115H-014; B1999-12-0520F-095

TI Properties of GaN homoepitaxial layers grown on GaN epitaxial wafers.

AU Dmitriev, V.; Nikolaev, A. (A.F. Ioffe Physicotech. Inst., Acad. of Sci., St. Petersburg, Russia); Cherenkov, A.; Tsvetkov, D.; Stepanov, S.; Kuznetsov, N.; Nikitina, I.; Kovarsky, A.; Yagovkina, M.; Davidov, V.

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Temperature. Symposium

Editor(s): DenBaars, S.; Palmour, J.; Shur, M.; Spencer, M.

Warrendale, PA, USA: Mater. Res. Soc, 1998. p. 451-6 of xiii+565 pp. 14 refs.

Conference: San Francisco, CA, USA, 13-15 April 1998

ISBN: 1-55899-418-1

DT Conference Article

TC Practical; Experimental

CY United States

LA English

L1 ANSWER 40 OF 63 INSPEC (C) 2004 IEE on STN

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AN 1999:6386564 INSPEC DN A1999-23-0762-006; B1999-12-72300-007

TI The effect of threading dislocations, Mg doping, and etching on the spectral responsivity in GaN-based ultraviolet detectors.

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S0 Journal of Applied Physics (15 Oct. 1999) vol. 86, no. 8, p. 4588-93. 32 refs.

Doc. No.: S0021-8979(99)09820-5

Published by: AIP

Price: CCCC 0021-8979/99/86(8)/4588(6)/\$15.00

CODEN: JAPIAU ISSN: 0021-8979

SICI: 0021-8979(19991015)86:8L.4588:ETDD;1-7

DT Journal

TC Application; Experimental

CY United States

LA English

L1 ANSWER 41 OF 63 INSPEC (C) 2004 IEE on STN

Full Text	References
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AN 1999:6325956 INSPEC DN A1999-19-8115G-001; B1999-10-0520D-001

TI Semi-insulating C-doped GaN and high-mobility AlGaIn/GaN heterostructures grown by ammonia molecular beam epitaxy.

AU Webb, J.B.; Tang, H.; Rolfe, S.; Bardwell, J.A. (Inst. for Microstruct. Sci., Nat. Res. Council of Canada, Ottawa, Ont., Canada)

S0 Applied Physics Letters (16 Aug. 1999) vol. 75, no. 7, p. 953-5. 17 refs.

Doc. No.: S0003-6951(99)00933-X

Published by: AIP

Price: CCCC 0003-6951/99/75(7)/953(3)/\$15.00

CODEN: APPLAB ISSN: 0003-6951

SICI: 0003-6951(19990816)75:7L.953:SIDH;1-5

DT Journal

TC Practical; Experimental

CY United States

LA English

L1 ANSWER 42 OF 63 INSPEC (C) 2004 IEE on STN

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 TI Optical properties of a high-quality **insulating GaN** epilayer.
 AU Zeng, K.C.; Lin, J.Y.; Jiang, H.X. (Dept. of Phys., Kansas State Univ.,
 Manhattan, KS, USA); Wei Yang
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 Doc. No.: S0003-6951(99)04025-5
 Published by: AIP
 Price: CCCC 0003-6951/99/74(25)/3821(3)/\$15.00
 CODEN: APPLAB ISSN: 0003-6951
 SICI: 0003-6951(19990621)74:25L:3821:OPHQ;1-G
 DT Journal
 TC Experimental
 CY United States
 LA English

L1 ANSWER 43 OF 63 INSPEC (C) 2004 IEE on STN

Full Text	Citing References
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AN 1999:6254375 INSPEC DN A1999-13-6150C-001; B1999-07-0510-001
 TI Near defect free GaN substrates.
 AU Porowski, S. (High Pressure Res. Center, Polish Acad. of Sci., Warsaw,
 Poland)
 SO MRS Internet Journal of Nitride Semiconductor Research (1999) vol.4S1. 37
 refs.
 Collection URL: <http://nsr.mii.mrs.org/>
 Published by: Mater. Res. Soc
 CODEN: MIJNF7 ISSN: 1092-5783
 DT Journal
 TC General Review; Experimental
 CY United States
 LA English

L1 ANSWER 44 OF 63 INSPEC (C) 2004 IEE on STN

Full Text	Citing References
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AN 1999:6156537 INSPEC DN A1999-06-7865K-008; B1999-03-2530C-038
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 AU Jiang, H.X.; Lin, J.Y. (Dept. of Phys., Kansas State Univ., Manhattan, KS,
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 Published by: SPIE-Int. Soc. Opt. Eng
 Price: CCCC 0277-786X/98/\$10.00
 CODEN: PSISDG ISSN: 0277-786X
 SICI: 0277-786X(1998)3277L:108:DFOT;1-Y
 Conference: Ultrafast Phenomena in Semiconductors II. San Jose, CA, USA,
 28-29 Jan 1998
 Sponsor(s): SPIE
 DT Conference Article; Journal

TC Experimental
CY United States
LA English

L1 ANSWER 45 OF 63 INSPEC (C) 2004 IEE on STN

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AN 1998:6015588 INSPEC DN A9820-7320-027; B9810-2520D-014
TI Magnetic resonance of dopants and defects in GaN-based materials and devices.
AU Carlos, W.E. (Naval Res. Lab., Washington, DC, USA)
S0 7th International Conference on Shallow-Level Centers in Semiconductors
Editor(s): Ammerlaan, C.A.J.; Pajot, B.
Singapore: World Scientific, 1997. p.13-23 of xviii+534 pp. 37 refs.
Conference: Amsterdam, Netherlands, 17-19 July 1996
Sponsor(s): Found. Phys.; Found. Fundamental Res. Matter; Philips Res.;
Int. Sci. Found.; Univ. Amsterdam
ISBN: 981-02-2928-3
DT Conference Article
TC Experimental
CY Singapore
LA English

L1 ANSWER 46 OF 63 INSPEC (C) 2004 IEE on STN

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AN 1998:5907712 INSPEC DN A9812-7360F-001; B9806-2520D-027
TI Deep centers in n-GaN grown by reactive molecular beam epitaxy.
AU Fang, Z.-Q.; Look, D.C. (Res. Center, Wright State Univ., Dayton, OH, USA); Kim, W.; Fan, Z.; Botchkarev, A.; Morkoc, H.
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Doc. No.: S0003-6951(98)02818-6
Published by: AIP
Price: CCCC 0003-6951/98/72(18)/2277(3)/\$15.00
CODEN: APPLAB ISSN: 0003-6951
SICI: 0003-6951(19980504)72:18L:2277:DCGR;1-G
DT Journal
TC Experimental
CY United States
LA English

L1 ANSWER 47 OF 63 INSPEC (C) 2004 IEE on STN

[Full Text](#) [References](#)

AN 1998:5808269 INSPEC DN A9804-7855-045
TI Photoluminescence of Fe-complexes in GaN.
AU Thurian, P.; Hoffmann, A.; Eckey, L.; Maxim, P.; Heitz, R.; Broser, I.
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Meyer, B.-K.; Schneider, J.; Bauer, J.; Kunzer, M.
S0 III-V Nitrides. Symposium
Editor(s): Ponce, F.A.; Moustakas, T.D.; Akasaki, I.; Monemar, B.A.

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DT Conference Article

TC Experimental

CY United States

LA English

L1 ANSWER 48 OF 63 INSPEC (C) 2004 IEE on STN

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AN 1998:5800812 INSPEC DN A9804-6170B-002

TI Investigation of vacancies in GaN by positron annihilation.

AU Jorgensen, L.V.; Kruseman, A.C.; Schut, H.; Van Veen, A. (Interfaculty Reactor Inst., Delft Univ. of Technol., Netherlands); Fanciulli, M.; Moustakas, T.D.

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Editor(s): Ponce, F.A.; Moustakas, T.D.; Akasaki, I.; Monemar, B.A.

Pittsburgh, PA, USA: Mater. Res. Soc, 1997. p.853-8 of xxv+1251 pp. 24 refs.

Conference: Boston, MA, USA, 2-6 Dec 1996

DT Conference Article

TC Experimental

CY United States

LA English

L1 ANSWER 49 OF 63 INSPEC (C) 2004 IEE on STN

Full Text	Cited References
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AN 1997:5780136 INSPEC DN A9802-7360F-015; B9801-2520D-079

TI Fe-related defects in GaN epilayers.

AU Thurian, P.; Heitz, R.; Eckey, L.; Maxim, P.; Kutzer, V.; Hoffmann, A.; Broser, I. (Inst. fur Festkorperphys., Tech. Univ. Berlin, Germany); Pressel, K.; Meyer, B.-K.

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Editor(s): Scheffler, M.; Zimmermann, R.

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(xxxviii+xxvii+xxx+xxvi+3460) pp. 6 refs.

Conference: Berlin, Germany, 21-26 July 1996

ISBN: 981-02-2777-9

DT Conference Article

TC Experimental

CY Singapore

LA English

L1 ANSWER 50 OF 63 INSPEC (C) 2004 FIZ KARLSRUHE on STN

Full Text	Cited References
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TC Experimental
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TC Practical; Experimental
CY United States
LA English

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CY United States
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TC Experimental
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